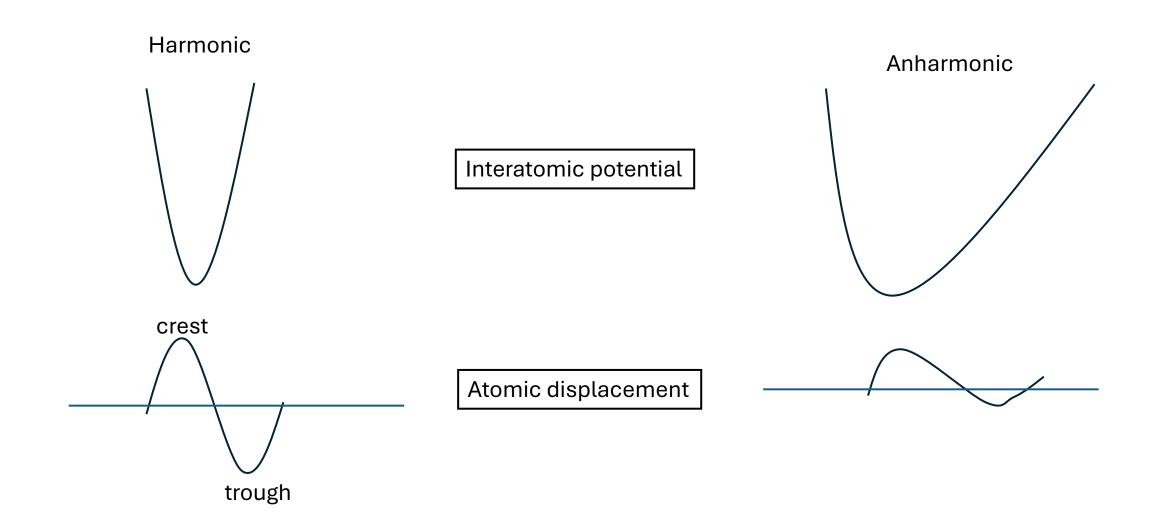
Anharmonicity and third-order elastic constants in silicon

A finite Grüneisen parameter implies asymmetry between atomic displacements at the crest (expansion) and trough (compression) of a longitudinal lattice vibration.

Fundamentally, this is a consequence of the anharmonicity of the interatomic (Lennard-Jones) potential.



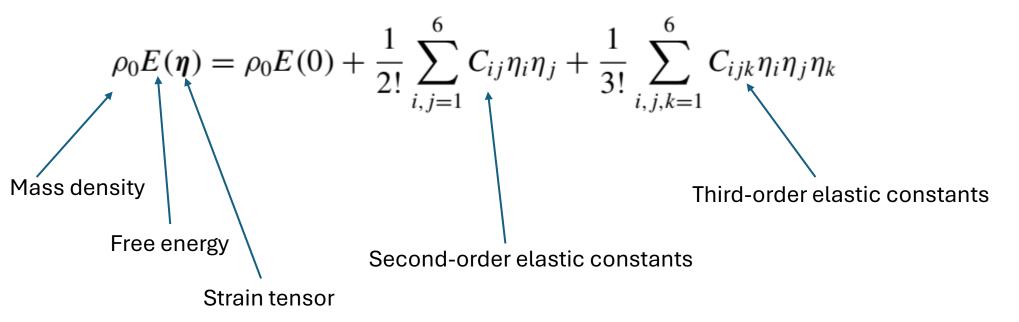
One way to quantify anharmonicity is to look at higher order elastic constants

First-principles calculation of higher-order elastic constants using exact deformation-gradient tensors

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(Received 12 June 2020; revised 18 September 2020; accepted 8 October 2020; published 23 October 2020)

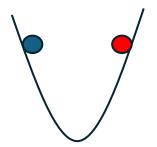


Harmonic and anharmonic cases

Harmonic

$$\rho_0 \frac{\partial E}{\partial \eta_i} = \frac{1}{2!} \sum_{j=1}^6 C_{ij} \eta_j$$

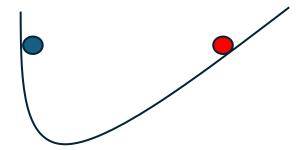
 $\eta_{crest} = \eta_{trough} = \eta_{average}$



Anharmonic

$$\rho_0 \frac{\partial E}{\partial \eta_i} = \frac{1}{2!} \sum_{j=1}^6 C_{ij} \eta_j + \frac{1}{3!} \sum_{j,k=1}^6 C_{ijk} \eta_j \eta_k$$

$$(\eta_{crest} - \eta_{trough})/\eta_{average} \approx \frac{\langle C_{ijK} \rangle}{3\langle C_{ij} \rangle}$$



The ratio of third-order to second-order elastic constants is a measure of anharmonicity!

Elastic constants of silicon in GPa

Second order

Constant	Value (GPa)	
C ₁₁	165.7	
C ₁₂	63.9	
C ₄₄	79.6	

Average:103 GPa

Third order

Constant	Value (GPa)	Uncertainty	
C ₁₁₁	-760	±20	
C ₁₁₂	-430	±20	
C ₁₂₃	-90	±20	
C ₁₄₄	+.20	±10	
C ₁₅₅	-690 ±20		
C ₄₅₆	-80	±10	

Sources:

- https://sense.fas.sfu.ca/internal/Si_elastic.pdf
- M. A. Hopcroft J. Micromech. Syst. 19, 229 (2010)
- N. P. Keating, Phys. Rev. 149, 674 (1966)

Average:338 GPa

How anharmonic is silicon?

$$(\eta_{crest} - \eta_{trough})/\eta_{average} \approx \frac{\langle C_{ijK} \rangle}{3\langle C_{ij} \rangle} \approx 1.1$$

How anharmonic is silicon?

Its Grüneisen parameter is of the order of unity!

$$\gamma_i = \frac{\partial ln\omega_i}{lnV} \approx -1$$

PHYSICAL REVIEW B 72, 014308 (2005)

Lattice thermal conductivity of silicon from empirical interatomic potentials

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TABLE I. Mode Grüneisen parameters for the Tersoff EIP calculated using three different parameter sets as described in the text and compared to experimental values from Ref. 36.

	Set B	Set C	Set B*	Experiment
$\gamma_{LTO}(\Gamma)$	1.33	1.32	1.39	0.98 ± 0.06
$\gamma_{TA}(X)$	-6.46	-0.20	-0.91	-1.4 ± 0.3
$\gamma_{TO}(X)$	1.66	1.60	1.71	1.5 ± 0.1
$\gamma_{TA}(L)$	-3.13	-0.31	-1.24	-1.3 ± 0.3
$\gamma_{TO}(L)$	1.48	1.45	1.55	1.3 ± 0.2